

2SK1254(L), 2SK1254(S)

Silicon N Channel MOS FET

REJ03G0917-0200 (Previous: ADE-208-1255) Rev.2.00 Sep 07, 2005

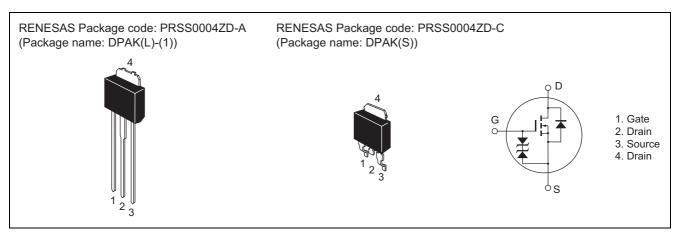
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline





Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	120	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	ID	3	А
Drain peak current	I _{D(pulse)} *1	12	А
Body to drain diode reverse drain current	I _{DR}	3	А
Channel dissipation	Pch∗ ₂	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

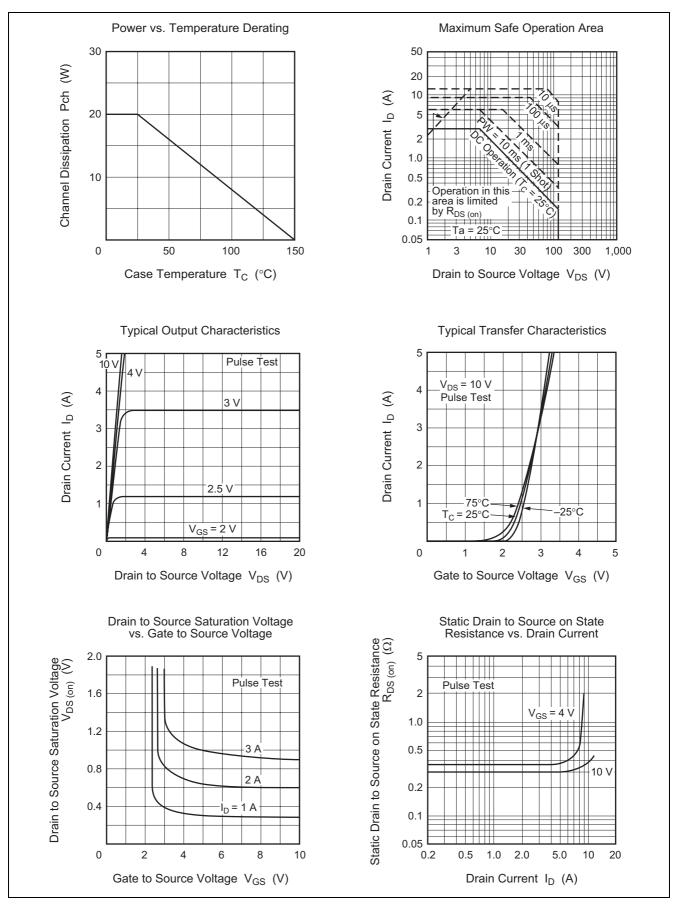
2. Value at $T_C = 25^{\circ}C$

Electrical Characteristics

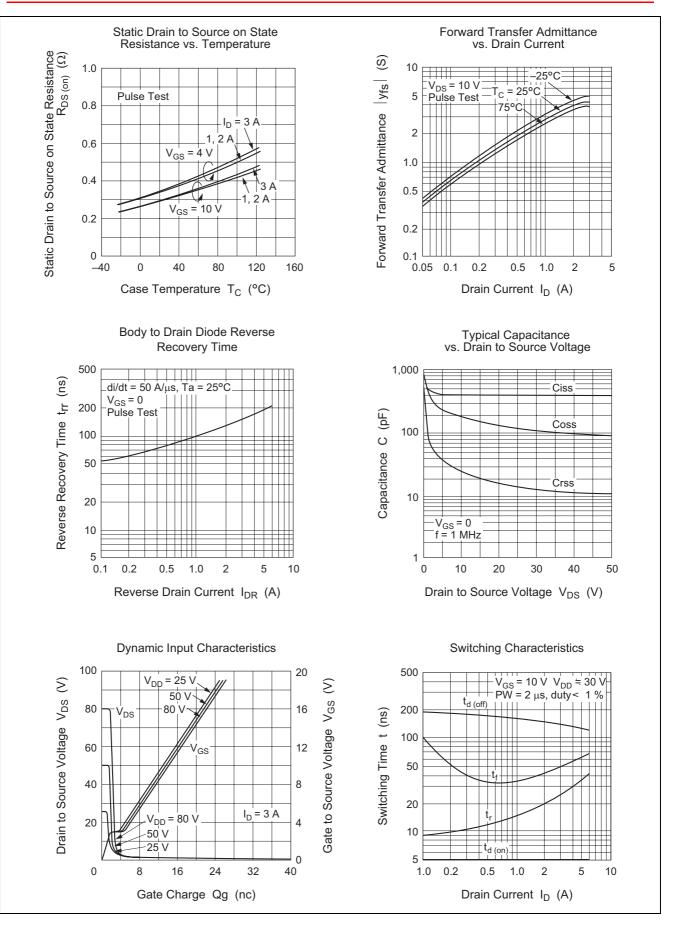
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	120	—	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	V _{(BR)GSS}	±20	—	—	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	—	±10	μΑ	$V_{GS} = \pm 16 V, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	100	μΑ	$V_{DS} = 100 V, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	1.0	—	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R _{DS(on)}		0.30	0.40	Ω	$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$
resistance			0.35	0.55	Ω	$I_D = 2 A, V_{GS} = 4 V^{*3}$
Forward transfer admittance	y _{fs}	2.4	4.0		S	$I_D = 2 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$
Input capacitance	Ciss	_	420	_	pF	$V_{DS} = 10 V, V_{GS} = 0,$
Output capacitance	Coss		190		pF	f = 1 MHz
Reverse transfer capacitance	Crss		25		pF	
Turn-on delay time	t _{d(on)}		5		ns	$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	tr		20		ns	R _L = 15 Ω
Turn-off delay time	t _{d(off)}		150		ns	
Fall time	t _f		45		ns	
Body to drain diode forward voltage	V_{DF}		0.95		V	$I_F = 3 A, V_{GS} = 0$
Body to drain diode reverse recovery	t _{rr}		160		ns	$I_F = 3 A, V_{GS} = 0,$
time						di _F /dt = 50 A/μs

Note: 3. Pulse test

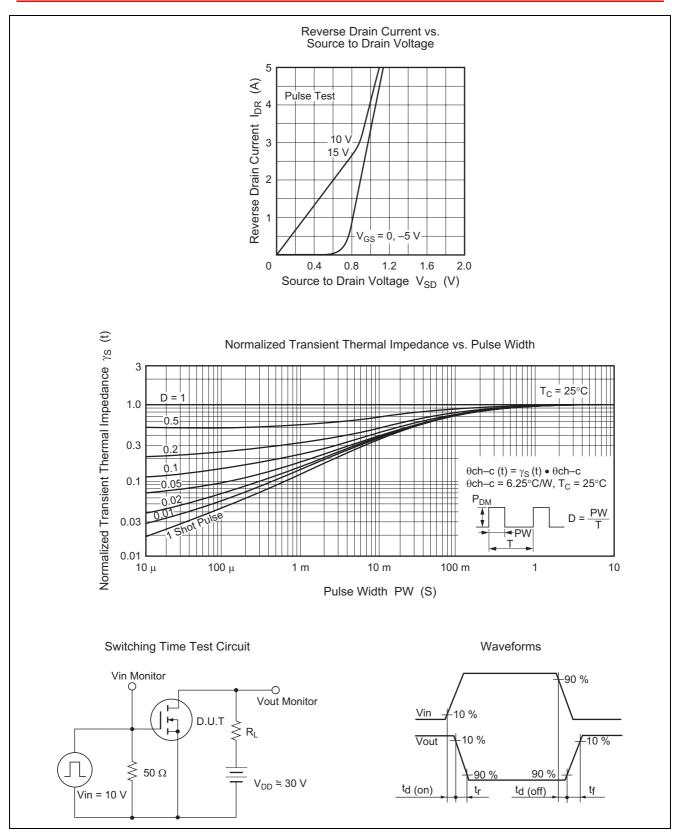
Main Characteristics





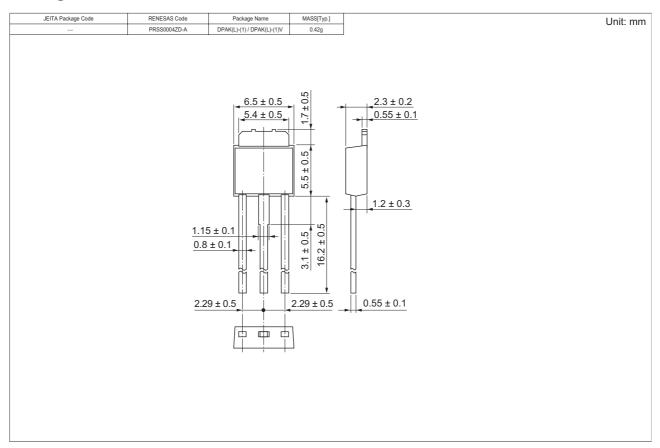


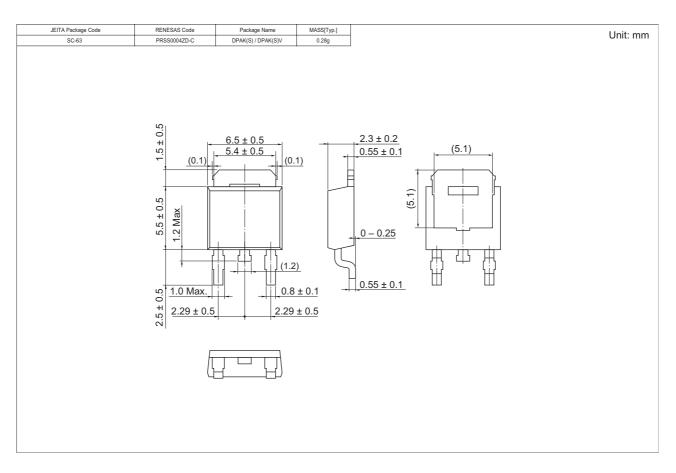






Package Dimensions







Ordering Information

Part Name	Quantity	Shipping Container
2SK1254L-E	3200 pcs	Box (Sack)
2SK1254STL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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